

METHOD OF FORMING A SEMICONDUCTOR DEVICE HAVING AIR GAPS AND THE STRUCTURE SO FORMED

Abstract

A method of forming a semiconductor device, and the device so formed. Depositing alternating layers of a first and a second dielectric material, wherein the first and second dielectric materials are selectively etchable at different rates. Forming a first feature within the alternating layers of dielectric material. Selectively etching the alternating layers of dielectric material to remove at least a portion of the first dielectric material in each layer having the first dielectric material and leaving the second dielectric material as essentially unetched.